

N-channel TrenchMOS standard level FET Rev. 3 — 23 February 2011

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference	data					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _j = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	75	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	167	W
Static cha	aracteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>		-	5.9	7	mΩ



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A}; V_{sup} \leq 30 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 10 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	329	mJ
Dynamic ch	naracteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 24 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	10	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK7207-30B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

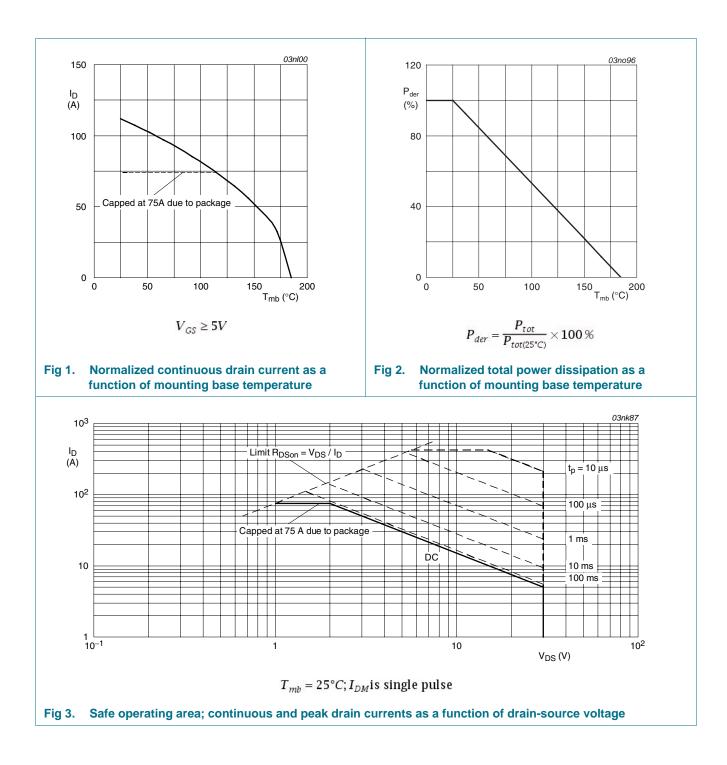
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 185 °C	-	30	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	30	V
V _{GS}	gate-source voltage		-20	20	V
	drain current	V_{GS} = 10 V; T _j = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u> _	112	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[2] _	75	А
		$V_{GS} = 10 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	<u>[2]</u> _	75	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _j = 25 °C; see <u>Figure 3</u>	-	449	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	167	W
T _{stg}	storage temperature		-55	185	°C
Tj	junction temperature		-55	185	°C
Source-drain	diode				
Is	source current	T _{mb} = 25 °C	[2]	75	А
			<u>[1]</u> _	112	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	449	А
Avalanche ru	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 75 A; V _{sup} ≤ 30 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped	-	329	mJ

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

BUK7207-30B

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5. Thermal characteristics

Parameter	Conditions	Min	Тур	Max	Unit
thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
thermal resistance from junction to ambient		-	71.4	-	K/W
	thermal resistance from junction to mounting base	thermal resistance from junction to mounting see Figure 4 base	thermal resistance from junction to mounting see Figure 4 - base	thermal resistance from junction to mounting see Figure 4 base	thermal resistance from junction to mounting see <u>Figure 4</u> 0.95 base

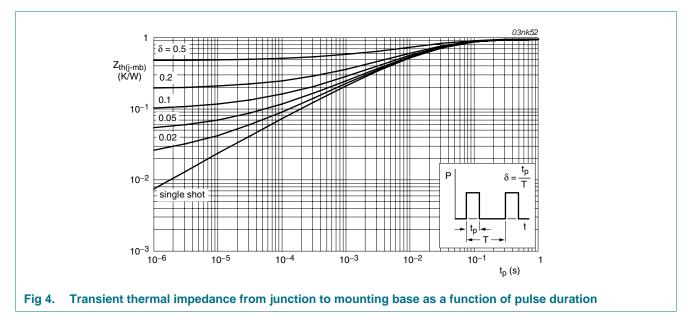


Table 5. Thermal characteristics

6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
	breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 185 \text{ °C};$ see <u>Figure 10</u>	0.9	-	-	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	4.4	V	
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 185 \text{ °C}$	-	-	500	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 185 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	13.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	5.9	7	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{12}$	-	34	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 24 V; V _{GS} = 10 V; T _j 25 °C; see <u>Figure 13</u>	-	8	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{12}$	-	10	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1684	2245	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	625	750	pF
C _{rss}	reverse transfer capacitance		-	249	314	pF
t _{d(on)}	turn-on delay time		-	14	-	ns
t _r	rise time		-	85	-	ns
d(off)	turn-off delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	55	-	ns
^l f	fall time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	76	-	ns
ЬD	internal drain inductance	measured from drain to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad; $T_i = 25 \text{ °C}$	-	7.5	-	nH

Symbol

Source-drain diode

BUK7207-30B

Max

Unit

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Тур

Min

D	source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0$ see <u>Figure 15</u>	v, 1j – 25° O,			1.2	V
	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -$		-	43	-	ns
	recovered charge	V _{GS} = -10 V; V _{DS} =	25 V; T _j = 25 °C	-	20	-	nC
400		03nk84	10			03nk83	
400 I _D 20	10 Lab	el is V _{GS} (V)	12 R _{DSon}				
(Ā) 14	9.5		(mΩ)				
^{300 –} 12	9 8.5		10				
200	8						
200	7 6.5		8				
100 —	6		6				
	5.5						
٥K	4.5		4				
Č A	0 1 0	a 1a		10	. –	20)
0	2 4 6	8 10 V _{DS} (V)	5	10	15 V	′ _{GS} (V)	
0	$T_j = 25^{\circ}C; t_p = 300\mu$	V _{DS} (V)	5		I_D^{15}	/ _{GS} (V)	
ig 5. Outj		V _{DS} (V) µs n current as a	5 Fig 6. Drain-sc		$C; I_D = 25A$	r _{GS} (V) Ince as a f	
ig 5. Outj func	$T_j = 25^{\circ}C; t_p = 300p$	V _{DS} (V) µs n current as a	5 Fig 6. Drain-so of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	r _{GS} (V) Ince as a f	
ig 5. Out func	$T_j = 25^{\circ}C; t_p = 300p$	V _{DS} (V) µs n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
ig 5. Out ₁ func	$T_j = 25^{\circ}C; t_p = 300p$	V _{DS} (V) µs n current as a tage; typical values	5 Fig 6. Drain-so of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
ig 5. Out func	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V _{DS} (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
ig 5. Out ₁ func	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V _{DS} (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
ig 5. Out func 10^{-1} I_D (A) 10^{-2}	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V _{DS} (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
ig 5. Outj func 10^{-1} I_D (A) 10^{-2} 10^{-3}	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V _{DS} (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
ig 5. Out func 10^{-1} I_D (A) 10^{-2}	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V _{DS} (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
$\begin{array}{c} 10^{-1} \\ I_D \\ (A) \\ 10^{-2} \\ 10^{-3} \end{array}$	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V _{DS} (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
ig 5. Out function $I_D^{10^{-1}}$ (A) I_D^{-2} I_D^{-3} I_D^{-4} I_D^{-5}	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V _{DS} (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	(_{GS} (V) Ice as a f Values	
ig 5. Out function $I_D^{10^{-1}}$ (A) I_D^{-2} I_D^{-3} I_D^{-4}	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain tion of drain-source volt	V _{DS} (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$ ate resistan age; typical	(_{GS} (V) Ice as a f Values	unction
ig 5. Out function 10^{-1} function 10^{-1} function (A) function 10^{-2} function 10^{-2} function 10^{-3} function 10^{-4} function 10^{-5} function 10^{-6} functi	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain tion of drain-source volt	V _{DS} (V) µs n current as a tage; typical values 032835 max max max Max Max Max Max Max Max Max M	5 Fig 6. Drain-sc of gate-s	T _j = 25°C	$C; I_D = 25A$ ate resistan age; typical	CGS (V)	unction

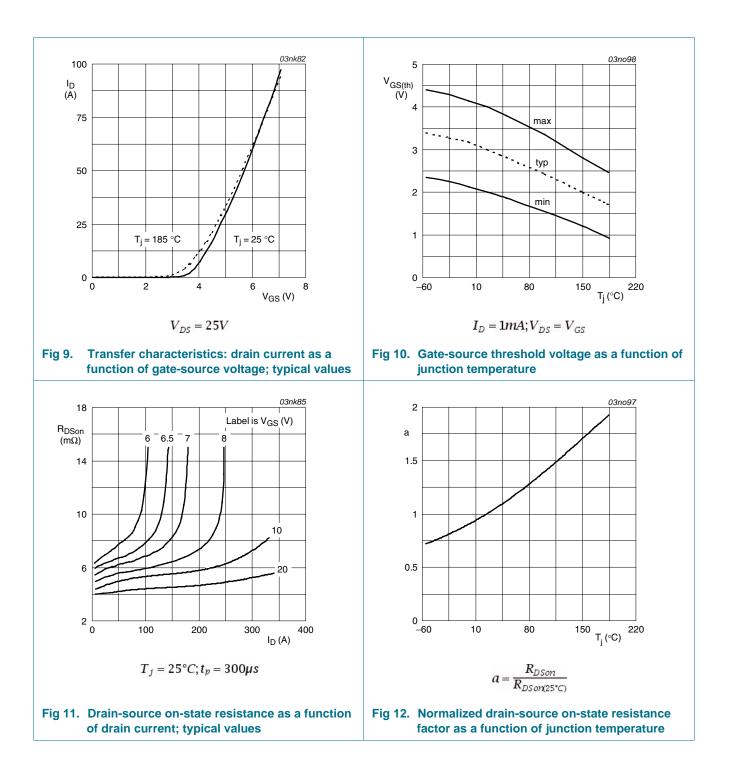
Table 6. Characteristics ... continued

Parameter

Conditions

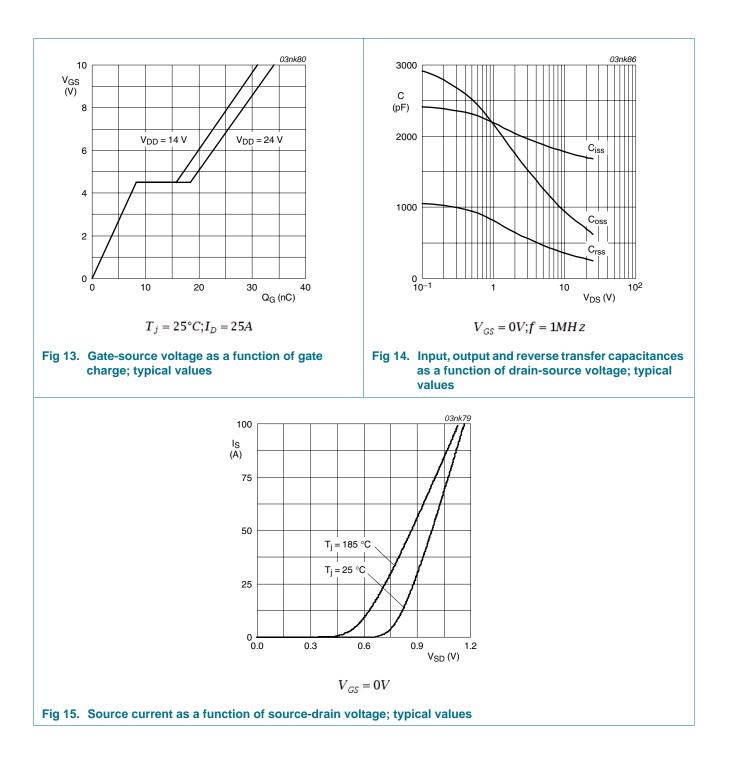
BUK7207-30B

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7. Package outline

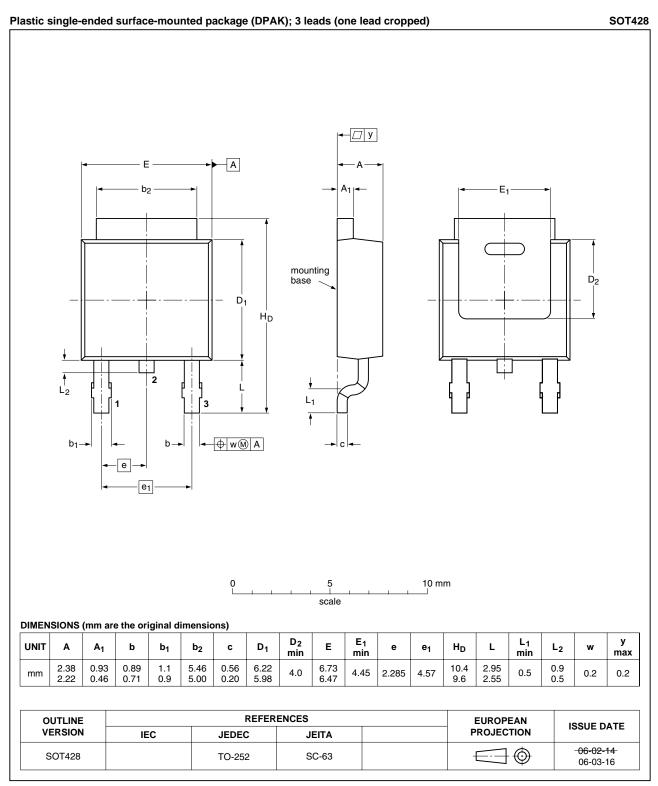


Fig 16. Package outline SOT428 (DPAK)

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8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7207-30B v.3	20110223	Product data sheet	-	BUK7207_30B-02
Modifications:	of NXP Semic	this data sheet has been rec conductors. we been adapted to the new		
BUK7207_30B-02 (9397 750 12227)	20040122	Product data	-	BUK7207_30B-01

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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